

TO-92 Plastic-Encapsulate Transistors

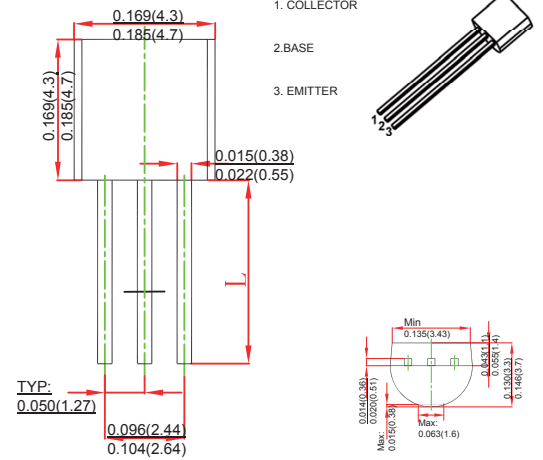
FEATURES

- Power dissipation
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BC327	-50
		BC328	-30
V_{CEO}	Collector-Emitter Voltage	BC327	-45
		BC328	-25
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-800	mA
P_C	Collector Power Dissipation	625	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ C$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage BC327 BC328	V_{CBO}	$I_C = -100\mu A, I_E = 0$	-50 -30			V
Collector-emitter breakdown voltage BC327 BC328	V_{CEO}	$I_C = -10mA, I_B = 0$	-45 -25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current BC327 BC328	I_{CBO}	$V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$			-0.1 -0.1	μA
Collector cut-off current BC327 BC328	I_{CEO}	$V_{CE} = -40V, I_B = 0$ $V_{CE} = -20V, I_B = 0$			-0.2 -0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		630	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -300mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -300mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	260			MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0$ $f = 1MHz$		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range	100-250	160-400	250-630

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

